

Ke-Meng Yang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8603566/publications.pdf>

Version: 2024-02-01

14
papers

106
citations

1478505

6
h-index

1372567

10
g-index

14
all docs

14
docs citations

14
times ranked

84
citing authors

#	ARTICLE	IF	CITATIONS
1	Snapback-Free Reverse-Conducting SOI LIGBT with an Integrated Self-Biased MOSFET. <i>Nanoscale Research Letters</i> , 2022, 17, 46.	5.7	1
2	The Application of the High-k Dielectrics in Lateral Double-Diffused Metal Oxide Semiconductor. , 2021, , ,		0
3	An Analytical Breakdown Model for the SOI LDMOS With Arbitrary Drift Doping Profile by Using Effective Substrate Voltage Method. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 49-56.	2.1	5
4	Numerical and analytical investigations for the SOI LDMOS with alternated high-k dielectric and step doped silicon pillars*. <i>Chinese Physics B</i> , 2020, 29, 038503.	1.4	8
5	The New Structure and Analytical Model of a High-Voltage Interconnection Shielding Structure With High- k Dielectric Pillar. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 1745-1750.	3.0	5
6	Analytical Model for the SOI Lateral Power Device With Step Width Technique and High- k Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 3055-3059.	3.0	9
7	Modeling of the Variation of Lateral Doping (VLD) Lateral Power Devices via 1-D Analysis Using Effective Concentration Profile Concept. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 990-996.	2.1	6
8	Area-Efficient and Snapback-Free SOI LIGBT With L-Shaped Extraction Path. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 728-734.	2.1	3
9	A New Low Turn-Off Loss SOI Lateral Insulated Gate Bipolar Transistor With Buried Variation of Lateral Doping Layer. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 62-69.	2.1	6
10	A New Physical Insight for the 3-D-Layout-Induced Cylindrical Breakdown in Lateral Power Devices on SOI Substrate. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 1843-1848.	3.0	6
11	Effective Doping Concentration Theory: A New Physical Insight for the Double-RESURF Lateral Power Devices on SOI Substrate. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 648-654.	3.0	23
12	A Novel Variation of Lateral Doping Technique in SOI LDMOS With Circular Layout. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 1447-1452.	3.0	21
13	A Novel 3-D Analytical Method for Curvature Effect-Induced Electric Field Crowding in SOI Lateral Power Device. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 4359-4365.	3.0	8
14	A new physical insight of RESURF effects based on gradual charge appointment concept for bulk silicon lateral power devices. <i>Superlattices and Microstructures</i> , 2016, 92, 111-123.	3.1	5